

1N5817, 1N5819 SCHOTTKY DIODE

FEATURES

Power dissipation

$$P_D: 300 \text{ mW}(T_{amb}=25^\circ\text{C})$$

Collector current

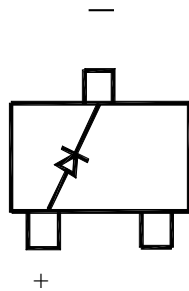
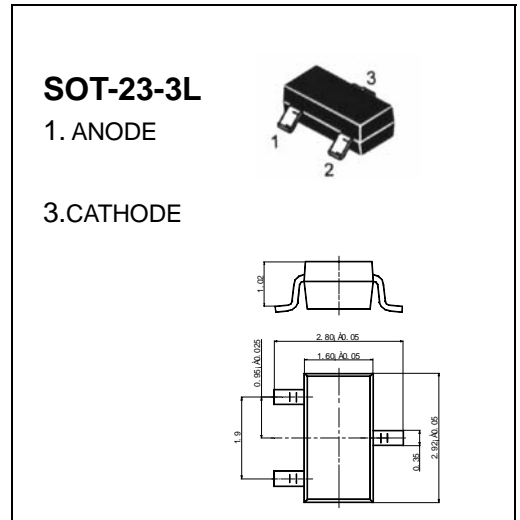
$$I_F : 1 \text{ A}$$

Collector-base voltage

$$V_R: \begin{matrix} 1N5817: & 20 & \text{V} \\ 1N5819: & 40 & \text{V} \end{matrix}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



1N5817 Marking: SJ
1N5819 Marking: SL

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _(BR) 1N5817 1N5819	I _R = 1mA	20 40		V
Reverse voltage leakage current	I _R	V _R =20V V _R =40V		1	mA
Forward voltage	1N5817 1N5819 V _F 1N5817 1N5819	I _F =1A* I _F =1A* I _F =3A* I _F =3A*		0.45 0.6 0.75 0.9	V
Diode capacitance	C _D	V _R =0V f=1MHz		120	pF

* 表示脉冲测试 t_p<300 μs, 占空比<2 %。